

High-Speed CAN Transceiver with Silent Mode - CAN FD Ready

Features

- Fully ISO 11898-2, ISO 11898-2: 2016 and SAE J2962-2 Compliant
- CAN FD Ready
- · Communication Speed up to 5 Mbit/s
- · ISO 26262 Functional Safety Ready
- Low Electromagnetic Emission (EME) and High Electromagnetic Immunity (EMI)
- Differential Receiver with Wide Common-Mode Range
- · Compatible to 3.3V and 5V Microcontrollers
- Functional Behavior Predictable under all Supply Conditions
- Transceiver Disengages from the Bus When Not Powered Up
- RXD Recessive Clamping Detection
- High Electrostatic Discharge (ESD) Handling Capability on the Bus Pins
- Bus Pins Protected Against Transients in Automotive Environments
- Transmit Data (TXD) Dominant Time-Out Function
- Undervoltage Detection on VCC and VIO Pins
- CANH/CANL Short-Circuit and Overtemperature
 Protected
- Fulfills the OEM "Hardware Requirements for LIN, CAN and FlexRay Interfaces in Automotive Applications", Rev. 1.3
- · AEC-Q100 and AEC-Q006 Qualified
- Two Ambient Temperature Grades Available:
 - ATA6564-GAQW1 and ATA6564-GBQW1 up to T_{amb} = +125°C
 - ATA6564-GAQW0 and ATA6564-GBQW0 up to T_{amb} = +150°C
- Packages: 8-pin SOIC, 8-pin VDFN with Wettable Flanks (Moisture Sensitivity Level 1)

Applications

Classical CAN and CAN FD networks in Automotive, Industrial, Aerospace, Medical and Consumer applications.

General Description

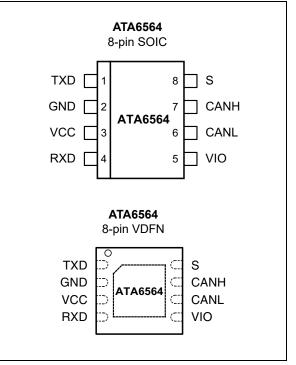
The ATA6564 is a high-speed CAN transceiver that provides an interface between a Controller Area Network (CAN) protocol controller and the physical Two-Wire CAN bus. The transceiver is designed for high-speed (up to 5 Mbit/s) CAN applications in the automotive industry, providing differential transmit and receive capability to (a microcontroller with) a CAN protocol controller.

It offers improved electromagnetic compatibility (EMC) and ESD performance as well as features such as:

- Ideal passive behavior to the CAN bus when the supply voltage is off
- Direct interfacing to microcontrollers with supply voltages from 3V to 5V

Two operating modes together with the dedicated fail-safe features make the ATA6564 an excellent choice for all types of high-speed CAN networks especially in nodes which do not require a Standby mode with wake-up capability via the bus.

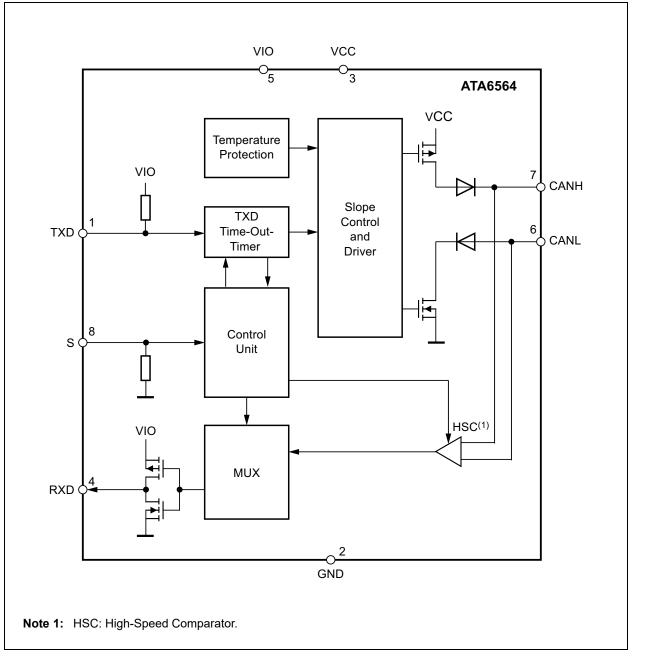
Package Types



ATA6564 Family Members

| Device | Grade 0 | Grade 1 | VDFN8 | SOIC8 | Description |
|---------------|---------|---------|-------|-------|---|
| ATA6564-GAQW0 | x | | | х | Silent mode, VIO - pin for compatibility with 3,3V and 5V microcontroller |
| ATA6564-GBQW0 | x | | x | | Silent mode, VIO - pin for compatibility with 3,3V and 5V microcontroller |
| ATA6564-GAQW1 | | X | | х | Silent mode, VIO - pin for compatibility with 3,3V and 5V microcontroller |
| ATA6564-GBQW1 | | Х | X | | Silent mode, VIO - pin for compatibility with 3,3V and 5V microcontroller |

Functional Block Diagram



1.0 FUNCTIONAL DESCRIPTION

The ATA6564 is a stand-alone high-speed CAN transceiver compliant with the ISO 11898-2, ISO 11898-2: 2016 and SAE J2962-2 CAN standards. It provides very low current consumption in Silent mode.

1.1 Operating Modes

The ATA6564 supports two operating modes: Silent and Normal. These modes can be selected via the S pin. See Figure 1-1 and Table 1-1 for a description of the operating modes.

1.1.1 NORMAL MODE

A low level on the S pin together with a high level on pin TXD selects the Normal mode. In this mode, the transceiver is able to transmit and receive data via the CANH and CANL bus lines (see Section "Functional Block Diagram"). The output driver stage is active and drives data from the TXD input to the CAN bus. The High-Speed Comparator (HSC) converts the analog data on the bus lines into digital data which is output to pin RXD. The bus biasing is set to $V_{VCC}/2$ and the undervoltage monitoring of VCC is active.

FIGURE 1-1: OPERATING MODES

The slope of the output signals on the bus lines is controlled and optimized in a way that ensures the lowest possible electromagnetic emission (EME).

To switch the device in normal operating mode, set the S pin to low and the TXD pin to high. See Table 1-1 and Figure 1-2. The S pin provides a pull-down resistor to GND, thus ensuring a defined level if the pin is open.

Please note that the device cannot enter Normal mode as long as TXD is at ground level.

1.1.2 SILENT MODE

A high level on the S pin selects Silent mode. This receive-only mode can be used to test the connection of the bus medium. In Silent mode the ATA6564 can still receive data from the bus, but the transmitter is disabled and therefore no data can be sent to the CAN bus. The bus pins are released to recessive state. All other IC functions, including the high-speed comparator (HSC), continue to operate as they do in Normal mode. Silent mode can be used to prevent a faulty CAN controller from disrupting all network communications.

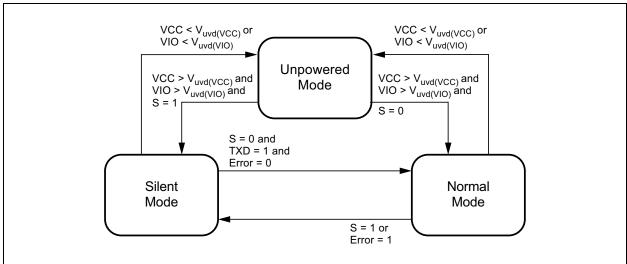


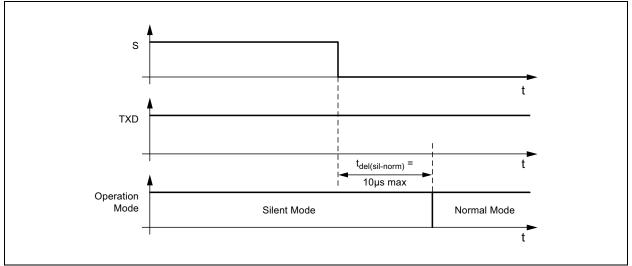
TABLE 1-1: OPERATING MODES

| Mode | Inp | outs | Outputs | | |
|-----------|------------------|------------------|------------|-----------------------|--|
| Mode | S Pin TXD | | CAN Driver | Pin RXD | |
| Unpowered | x ⁽²⁾ | x ⁽²⁾ | Recessive | Recessive | |
| Silent | HIGH | x ⁽²⁾ | Recessive | Active ⁽¹⁾ | |
| Normal | LOW | LOW | Dominant | LOW | |
| | LOW | HIGH | Recessive | HIGH | |

Note 1: LOW if the CAN bus is dominant, HIGH if the CAN bus is recessive.

2: Irrelevant





1.2 Fail-Safe Features

1.2.1 TXD DOMINANT TIME-OUT FUNCTION

A TXD dominant time-out timer is started when the TXD pin is set to low. If the low state on the TXD pin persists for longer than $t_{to(dom)TXD}$, the transmitter is disabled, releasing the bus lines to recessive state. This function prevents a hardware and/or software application failure from driving the bus lines to a permanent dominant state (blocking all network communications). The TXD dominant time-out timer is reset when the TXD pin is set to high. If the low state on the TXD pin was longer than $t_{to(dom)TXD}$, then the TXD pin has to be set to high longer 4 µs in order to reset the TXD dominant time-out timer.

1.2.2 INTERNAL PULL-UP/PULL-DOWN STRUCTURE AT THE TXD AND S INPUT PINS

The TXD pin has an internal pull-up resistor to VIO and the S pin an internal pull-down resistor to GND. This ensures a safe, defined state in case one or all of these pins are left floating.

1.2.3 UNDERVOLTAGE DETECTION ON PINS VCC AND VIO

If V_{VCC} or V_{VIO} drop below their respective undervoltage detection levels ($V_{uvd(VCC)}$ and $V_{uvd(VIO)}$ (see Section, Electrical Characteristics), the transceiver switches off and disengages from the bus until V_{VCC} and V_{VIO} have recovered. The logic state of the S pin is ignored until the VCC voltage or the VIO voltage has recovered.

1.2.4 OVERTEMPERATURE PROTECTION

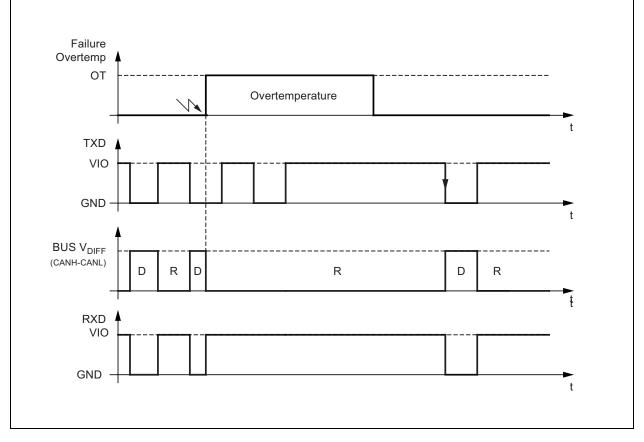
The output drivers are protected against overtemperature conditions. If the junction temperature exceeds the shutdown junction temperature, T_{Jsd} , the output drivers are disabled until the junction temperature drops below T_{Jsd} and pin TXD is at high level again. This ensures that output driver oscillations due to temperature drift are avoided. See Figure 1-3.

1.2.5 SHORT-CIRCUIT PROTECTION OF THE BUS PINS

The CANH and CANL bus outputs are short-circuit protected, either against GND or a positive supply voltage. A current-limiting circuit protects the transceiver against damage. If the device is heating up due to a continuous short on CANH or CANL, the internal overtemperature protection switches off the bus transmitter.

1.2.6 RXD RECESSIVE CLAMPING

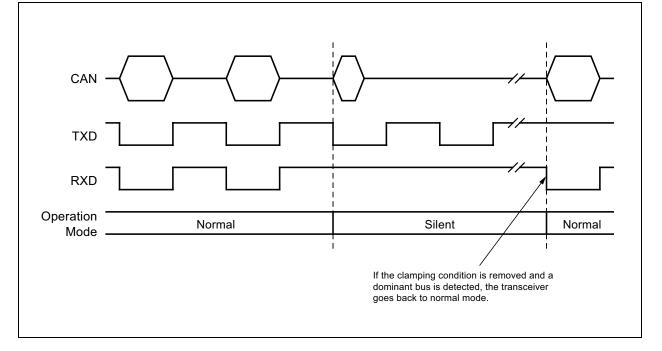
This fail-safe feature prevents the controller from sending data on the bus if its RXD line is clamped to HIGH (e.g., recessive). That is, if the RXD pin cannot signalize a dominant bus condition because it is e.g, shorted to VCC, the transmitter within ATA6564 is disabled to avoid possible data collisions on the bus. In Normal and Silent mode, the device permanently compares the state of the high-speed comparator (HSC) with the state of the RXD pin. If the HSC indicates a dominant bus state for more than t_{RC_det} without the RXD pin doing the same, a recessive clamping situation is detected and the device is forced into Silent mode. This Fail-safe mode is released by either entering Unpowered mode or if the RXD pin is showing a dominant (e.g., LOW) level again. See Figure 1-4.







RXD RECESSIVE CLAMPING DETECTION



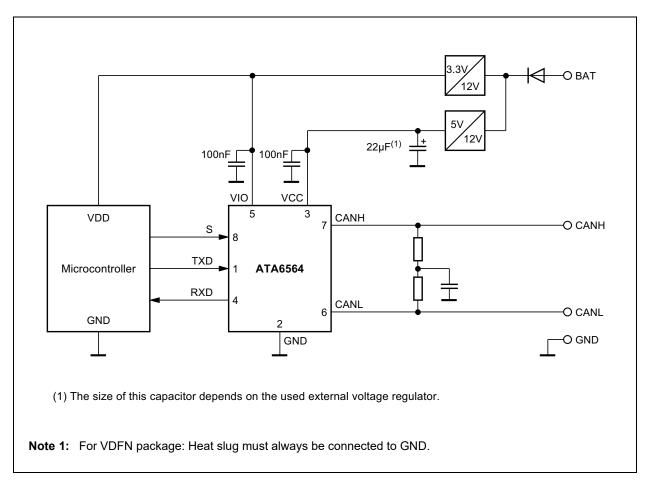
1.3 Pin Descriptions

The descriptions of the pins are listed in Table 1-2.

TABLE 1-2: PIN FUNCTION TABLE

| Pin Number | Pin Name | Description | | | | | |
|----------------------|--|--|--|--|--|--|--|
| 1 | TXD | Transmit data input | | | | | |
| 2 | GND | Ground | | | | | |
| 3 | VCC | Supply voltage | | | | | |
| 4 | RXD | Receive data output; reads out data from the bus lines | | | | | |
| 5 | VIO | Supply voltage for I/O level adapter | | | | | |
| 6 | CANL | Low-level CAN bus line | | | | | |
| 7 | CANH | High-level CAN bus line | | | | | |
| 8 | S | Silent mode control input | | | | | |
| 9 | 9 EP ⁽¹⁾ Exposed Thermal Pad: Heat slug, internally connected to the GND pin. | | | | | | |
| Note 1: Only for the | ne VDFN packa | age. | | | | | |

1.4 Typical Application



2.0 ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings^(†)

| Transient Voltage on CANH and CANL (ISO 7637 part 2) $-150V$ to $+100V$ Max. Differential Bus Voltage $-5V$ to $+18V$ DC Voltage on all other Pins $-0.3V$ to $+5.5V$ ESD on CANH and CANL Pins (IEC 61000-4-2) ± 8 kVESD (HBM following STM 5.1 with 1.5 k Ω /100 pF) (Pins CANH, CANL to GND) ± 6 kVComponent Level ESD (HBM according to ANSI/ESD STM 5.1) JESD22-A114, AEC-Q 100 (002) ± 4 kVCDM ESD STM 5.3.1 $\pm 750V$ ESD Machine Model AEC-Q100-RevF(003) $\pm 200V$ Virtual Junction Temperature -40° C to $+175^{\circ}$ CStorage Temperature -55° C to $+150^{\circ}$ C | DC Voltage at CANH and CANL | –27V to +42V |
|--|--|-----------------|
| $\begin{array}{llllllllllllllllllllllllllllllllllll$ | Transient Voltage on CANH and CANL (ISO 7637 part 2) | –150V to +100V |
| ESD on CANH and CANL Pins (IEC 61000-4-2) ±8 kV ESD (HBM following STM 5.1 with 1.5 kΩ/100 pF) (Pins CANH, CANL to GND) ±6 kV Component Level ESD (HBM according to ANSI/ESD STM 5.1) JESD22-A114, AEC-Q 100 (002) ±4 kV CDM ESD STM 5.3.1 ±750V ESD Machine Model AEC-Q100-RevF(003) ±200V Virtual Junction Temperature -40°C to +175°C | Max. Differential Bus Voltage | –5V to +18V |
| ESD (HBM following STM 5.1 with 1.5 kΩ/100 pF) (Pins CANH, CANL to GND) | DC Voltage on all other Pins | –0.3V to +5.5V |
| Component Level ESD (HBM according to ANSI/ESD STM 5.1) JESD22-A114, AEC-Q 100 (002) | ESD on CANH and CANL Pins (IEC 61000-4-2) | ±8 kV |
| CDM ESD STM 5.3.1 ±750V ESD Machine Model AEC-Q100-RevF(003) ±200V Virtual Junction Temperature -40°C to +175°C | ESD (HBM following STM 5.1 with 1.5 k Ω /100 pF) (Pins CANH, CANL to GND) | ±6 kV |
| ESD Machine Model AEC-Q100-RevF(003) | Component Level ESD (HBM according to ANSI/ESD STM 5.1) JESD22-A114, AEC-Q 100 (002) . | ±4 kV |
| Virtual Junction Temperature | CDM ESD STM 5.3.1 | ±750V |
| | ESD Machine Model AEC-Q100-RevF(003) | ±200V |
| Storage Temperature55°C to +150°C | Virtual Junction Temperature | –40°C to +175°C |
| | Storage Temperature | –55°C to +150°C |

† Notice: Stresses beyond those listed below may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ELECTRICAL CHARACTERISTICS

Electrical Specifications: Grade 1: T_{amb} = -40°C to +125°C, Grade 0: T_{amb} = -40°C to +150°C, $T_{vJ} \le 170$ °C, V_{VCC} = 4.5V to 5.5V; V_{VIO} = 2.8V to 5.5V; R_L = 60 Ω , C_L = 100 pF, unless otherwise specified. All voltages are defined in relation to ground; positive currents flow into the IC.

| in relation to ground; positive ci | urrents flow into | o the IC. | T | 1 | 1 | 1 |
|--|------------------------|----------------------|------|---------------------------|-------|--|
| Parameters | Symbol | Min. | Тур. | Max. | Units | Conditions |
| Supply, Pin VCC | | | | | | |
| Supply Voltage | V _{VCC} | 4.5 | — | 5.5 | V | |
| Supply Current in Silent Mode | I _{VCC_sil} | 1.9 | 2.5 | 3.2 | mA | Silent mode, V _{TXD} = V _{VIO} |
| | I _{VCC_rec} | 2 | — | 5 | mA | Recessive, V _{TXD} = V _{VIO} |
| Supply Current in Normal | I _{VCC_dom} | 30 | 50 | 70 | mA | Dominant, V _{TXD} = 0V |
| Mode | I _{VCC_short} | _ | _ | 85 | mA | Short between CANH and CANL (Note 1) |
| Undervoltage Detection Threshold on Pin VCC | V _{uvd(VCC)} | 2.75 | _ | 4.5 | V | |
| I/O Level Adapter Supply, Pin | VIO | | | | | |
| Supply Voltage on Pin VIO | V _{VIO} | 2.8 | — | 5.5 | V | |
| Supply Current on Din VIO | I _{VIO_rec} | 10 | 80 | 250 | μA | Normal and Silent mode Recessive, V _{TXD} = V _{VIO} |
| Supply Current on Pin VIO | I _{VIO_dom} | 50 | 350 | 500 | μA | Normal and Silent mode Dominant, V _{TXD} = 0V |
| Undervoltage Detection Threshold on Pin VIO | V _{uvd(VIO)} | 1.3 | _ | 2.7 | V | |
| Mode Control Input, Pin S | | | | | | |
| High-Level Input Voltage | V _{IH} | $0.7 \times V_{VIO}$ | — | V _{VIO} + 0.3 | V | |
| Low-Level Input Voltage | V _{IL} | -0.3 | — | $0.3 	imes V_{VIO}$ | V | |
| Pull-Down Resistor to GND | R_{pd} | 75 | 125 | 175 | kΩ | $V_{\rm S} = V_{\rm VIO}$ |
| Low-Level Leakage Current | ١ _L | -2 | — | +2 | μA | $V_{\rm S} = 0V$ |
| CAN Transmit Data Input, Pin | TXD | | | | | |
| High-Level Input Voltage | V _{IH} | $0.7 \times V_{VIO}$ | _ | V _{VIO} + 0.3 | V | |
| Low-Level Input Voltage | V _{IL} | -0.3 | _ | $0.3 \times V_{VIO}$ | V | |
| Pull-Up Resistor to VIO | R _{TXD} | 20 | 35 | 50 | kΩ | V _{TXD} = 0V |
| High-Level Leakage Current | I _{TDX} | -2 | — | +2 | μA | Normal mode, V _{TXD} = V _{VIO} |
| Input Capacitance | C _{TXD} | — | 5 | 10 | pF | Note 3 |
| CAN Receive Data Output, Pi | | | | | | |
| High-Level Output Current | I _{ОН} | -8 | — | -1 | mA | $V_{RXD} = V_{VIO} - 0.4V$, $V_{VIO} = V_{VCC}$ |
| Low-Level Output Current | I _{OL} | 2 | — | 12 | mA | V _{RXD} = 0.4V, Bus Dominant |
| | | | | | | J |

Note 1: 100% correlation tested.

2: Characterized on samples.

3: Design parameter.

ELECTRICAL CHARACTERISTICS (CONTINUED)

Electrical Specifications: Grade 1: $T_{amb} = -40^{\circ}C$ to +125°C, Grade 0: $T_{amb} = -40^{\circ}C$ to +150°C, $T_{vJ} \le 170^{\circ}C$, $V_{VCC} = 4.5V$ to 5.5V; $V_{VIO} = 2.8V$ to 5.5V; $R_L = 60\Omega$, $C_L = 100$ pF, unless otherwise specified. All voltages are defined in relation to ground; positive currents flow into the IC.

| Parameters | Symbol | Min. | Тур. | Max. | Units | Conditions |
|---|-------------------------|------|---------------------------|------|-------|--|
| Bus Lines, Pins CANH and C | CANL | | | | • | · |
| Single Ended Dominant Output Voltage | V _{O(dom)} | 2.75 | 3.5 | 4.5 | V | |
| Single Ended Dominant Output Voltage | V _{O(dom)} | 0.5 | 1.5 | 2.25 | V | |
| Transmitter Voltage Symmetry | V _{Sym} | 0.9 | 1 | 1.1 | _ | V _{Sym} = (V _{CANH} + V _{CANL}) /V _{VCC} (Note 3) |
| | | 1.5 | _ | 3 | V | V_{TXD} = 0V, t < t _{to(dom)TXD} R _L = 45 Ω to 65 Ω |
| Bus Differential Output | V _{Diff} | 1.5 | — | 3.3 | V | |
| Voltage | ♥ Diff | 1.5 | _ | 5 | V | |
| | | -50 | _ | +50 | mV | V_{VCC} = 4.75V to 5.25V V_{TXD} = V _{VIO} , receive, no load |
| Recessive Output Voltage | V _{O(rec)} | 2 | 0.5 x V _{VCC} | 3 | V | Normal and Silent mode, V _{TXD} = V _{VIO} , no load |
| Differential Receiver Threshold Voltage (HSC) | V _{th(RX)dif} | 0.5 | 0.7 | 0.9 | V | Normal and Silent mode, V _{cm(CAN)} = –27V to +27V |
| Differential Receiver Hysteresis Voltage (HSC) | V _{hys(RX)dif} | 50 | 120 | 200 | mV | Normal and Silent mode, V _{cm(CAN)} = –27V to +27V |
| Dominant Output Current | I _{IO(dom)} | -75 | | -35 | mA | $ \begin{array}{l} V_{TXD} = 0V, t < t_{to(dom)TXD,} \\ V_{VCC} = 5V \\ pin \ CANH, V_{CANH} = -5V \end{array} $ |
| Dominant Output Ourient | | 35 | | 75 | mA | |
| Recessive Output Current | I _{IO(rec)} | -5 | | +5 | mA | Normal and Silent mode, $V_{TXD} = V_{VIO}$, no load, $V_{CANH} = V_{CANL} = -27V$ to +32V |
| | | -5 | 0 | +5 | μA | $V_{VCC} = V_{VIO} = 0V,$ $V_{CANH} = V_{CANL} = 5V$ |
| Leakage Current | I _{IO(leak)} | -5 | 0 | +5 | μΑ | VCC = VIO connected to GND with $47k\Omega$ V _{CANH} = V _{CANL} = 5V (Note 3) |
| | | 9 | 15 | 28 | kΩ | $V_{CANH} = V_{CANL} = 4V$ |
| Input Resistance | R _i | 9 | 15 | 28 | kΩ | -2V ≤ V _{CANH} ≤ +7V, -2V ≤ V _{CANL} ≤ +7V (Note 3) |
| Input Resistance Deviation | | -1 | 0 | +1 | % | Between CANH and CANL $V_{CANH} = V_{CANL} = 4V$ |
| | ΔR _i | -1 | 0 | +1 | % | -2V ≤ V _{CANH} ≤ +7V, -2V ≤ V _{CANL} ≤ +7V (Note 3) |

Note 1: 100% correlation tested.

2: Characterized on samples.

3: Design parameter.

ELECTRICAL CHARACTERISTICS (CONTINUED)

Electrical Specifications: Grade 1: $T_{amb} = -40^{\circ}C$ to +125°C, Grade 0: $T_{amb} = -40^{\circ}C$ to +150°C, $T_{vJ} \le 170^{\circ}C$, $V_{VCC} = 4.5V$ to 5.5V; $V_{VIO} = 2.8V$ to 5.5V; $R_L = 60\Omega$, $C_L = 100$ pF, unless otherwise specified. All voltages are defined in relation to ground; positive currents flow into the IC.

| in relation to ground; positive c | | | _ | | | | | |
|---|------------------------------|------|------|------|-------|--|--|--|
| Parameters | Symbol | Min. | Тур. | Max. | Units | Conditions | | |
| | | 18 | 30 | 56 | kΩ | $V_{CANH} = V_{CANL} = 4V$ | | |
| Differential Input Resistance | R _{i(dif)} | 18 | 30 | 56 | kΩ | –2V ≤ V _{CANH} ≤ +7V, –2V ≤ V _{CANL} ≤ +7V (Note 3) | | |
| Common-Mode Input Capacitance | C _{i(cm)} | _ | _ | 20 | pF | f = 500 kHz, CANH and CANL referred to GND (Note 3) | | |
| Differential Input Capacitance | C _{i(dif)} | _ | _ | 10 | pF | f = 500 kHz, between CANH and CANL (Note 3) | | |
| Differential Bus Voltage Range for RECESSIVE State Detection | V _{Diff_rec} | -3 | _ | +0.5 | V | Normal and Silent mode (Note 3) $-27V \le V_{CANH} \le +27V$, $-27V \le V_{CANL} \le +27V$ | | |
| Differential Bus Voltage Range for DOMINANT State Detection | V_{Diff_dom} | 0.9 | _ | 8 | V | Normal and Silent mode (Note 3) -27V \leq V _{CANH} \leq +27V, -27V \leq V _{CANL} \leq +27V | | |
| Transceiver Timing, Pins CANH, CANL, TXD, and RXD, see Figure Figure 2-1 and Figure 2-2 | | | | | | | | |
| Delay Time from TXD to Bus Dominant | t _{d(TXD-busdom)} | 40 | _ | 130 | ns | Normal mode (Note 2) | | |
| Delay Time from TXD to Bus Recessive | t _{d(TXD-busrec)} | 40 | _ | 130 | ns | Normal mode (Note 2) | | |
| Delay Time from Bus Dominant to RXD | t _{d(busdom-RXD)} | 20 | _ | 100 | ns | Normal and Silent mode (Note 2) | | |
| Delay Time from Bus Recessive to RXD | t _{d(busrec-RXD)} | 20 | _ | 100 | ns | Normal and Silent mode (Note 2) | | |
| | | 40 | _ | 210 | ns | Normal mode, Rising edge at pin TXD R _L = 60Ω, C _L = 100 pF | | |
| Propagation Delay from TXD | | 40 | _ | 200 | ns | Normal mode, Falling edge at pin TXD $R_L = 60\Omega$, $C_L = 100 \text{ pF}$ | | |
| to RXD | TXD t _{PD(TXD-RXD)} | | | 300 | ns | Normal mode, Rising edge at pin TXD R _L = 150Ω, C _L = 100 pF (Note 3) | | |
| | | _ | _ | 300 | ns | Normal mode, Falling edge at pin TXD R _L = 150 Ω , C _L = 100 pF (Note 3) | | |
| TXD Dominant Time-out Time | t _{to(dom)TXD} | 0.8 | | 3 | ms | V _{TXD} = 0V, Normal mode | | |
| Delay Time for Normal Mode to Silent Mode Transition | t _{del(norm-sil)} | | | 10 | μs | Rising edge at pin S (Note 3) | | |
| Delay Time for Silent Mode to Normal Mode Transition | t _{del(sil-norm)} | _ | _ | 10 | μs | Falling edge at pin S (Note 3) | | |
| Debouncing Time for Recessive Clamping State Detection | t _{RC_det} | _ | 90 | | ns | V(CANH-CANL) > 900 mV RXD = HIGH (<mark>Note 3</mark>) | | |

Note 1: 100% correlation tested.

2: Characterized on samples.

3: Design parameter.

ELECTRICAL CHARACTERISTICS (CONTINUED)

Electrical Specifications: Grade 1: $T_{amb} = -40^{\circ}C$ to +125°C, Grade 0: $T_{amb} = -40^{\circ}C$ to +150°C, $T_{vJ} \le 170^{\circ}C$, $V_{VCC} = 4.5V$ to 5.5V; $V_{VIO} = 2.8V$ to 5.5V; $R_L = 60\Omega$, $C_L = 100$ pF, unless otherwise specified. All voltages are defined in relation to ground; positive currents flow into the IC.

| | | | _ | | | A 11/1 | | | |
|--|-----------------------|------|------|------|-------|--|--|--|--|
| Parameters | Symbol | Min. | Тур. | Max. | Units | Conditions | | | |
| Transceiver Timing for Higher Bit Rates, Pins CANH, CANL, TXD, and RXD, see Figure 2-1 and Figure 2-3, External Capacitor on the RXD Pin $C_{RXD} \le 20 \text{ pF}$ | | | | | | | | | |
| Recessive Bit Time on Pin RXD | t _{Bit(RXD)} | 400 | — | 550 | ns | Normal mode, $t_{Bit(TXD)} = 500$ ns (Note 1) $R_L = 60\Omega$, $C_L = 100 \text{ pF}$ | | | |
| | Dir(IO(D) | 120 | _ | 220 | ns | Normal mode, t _{Bit(TXD)} = 200 ns R _L = 60Ω, C _L = 100 pF | | | |
| Recessive Bit Time on the Bus | t _{Bit(Bus)} | 435 | _ | 530 | ns | Normal mode, $t_{Bit(TXD)} = 500 \text{ ns}$ (Note 1) $R_L = 60\Omega$, $C_L = 100 \text{ pF}$ | | | |
| | | 155 | _ | 210 | ns | Normal mode, t _{Bit(TXD)} = 200 ns R _L = 60Ω, C _L = 100 pF | | | |
| Possiver Timing Symmetry | ∆t _{Rec} - | -65 | — | +40 | ns | Normal mode, $t_{Bit(TXD)} = 500$ ns $\Delta t_{Rec} = t_{Bit(RXD)} - t_{Bit(Bus)}$ (Note 1) $R_L = 60\Omega$, $C_L = 100 \text{ pF}$ | | | |
| Receiver Timing Symmetry | | -45 | _ | +15 | ns | Normal mode, $t_{Bit(TXD)} = 200$ ns $\Delta t_{Rec} = t_{Bit(RXD)} - t_{Bit(Bus)}$ $R_L = 60\Omega$, $C_L = 100 \text{ pF}$ | | | |

Note 1: 100% correlation tested.

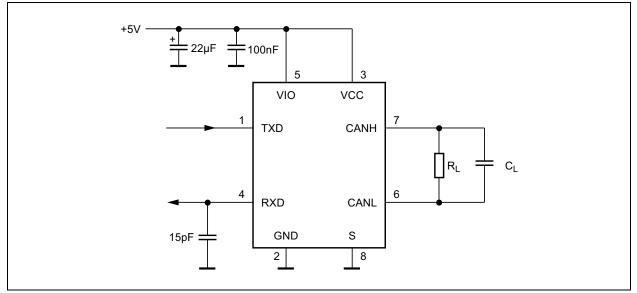
2: Characterized on samples.

3: Design parameter.

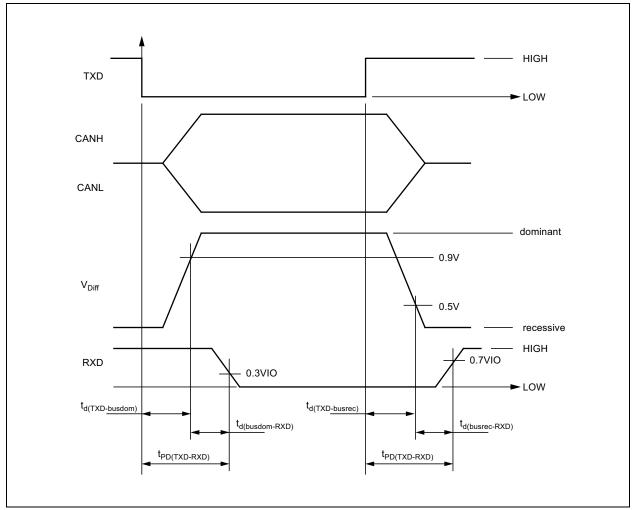
TABLE 2-1: TEMPERATURE SPECIFICATIONS

| Symbol | Min. | Тур. | Max. | Units |
|-----------------------|--|---|--|--|
| | | | | |
| R _{thvJA} | | 145 | | K/W |
| T _{vJsd} | 150 | _ | 195 | °C |
| T _{vJsd} | 170 | — | 195 | °C |
| T _{vJsd_hys} | _ | 15 | _ | °C |
| | | | | |
| R _{thvJC} | _ | 10 | _ | K/W |
| R _{thvJA} | | 50 | | K/W |
| T _{vJsd} | 150 | _ | 195 | °C |
| T _{vJsd} | 170 | _ | 195 | °C |
| T _{vJsd_hys} | _ | 15 | _ | °C |
| | R _{thvJA} T _{vJsd} T _{vJsd} T _{vJsd hys} R _{thvJC} R _{thvJA} T _{vJsd} | R_{thvJA} — T_{vJsd} 150 T_{vJsd} 170 T_{vJsd} 170 T_{vJsd} — R_{thvJC} — R_{thvJA} — T_{vJsd} 150 T_{vJsd} 170 | R _{thvJA} — 145 T _{vJsd} 150 — T _{vJsd} 170 — T _{thvJg} — 50 T _{vJsd} 150 — T _{vJsd} 170 — | R _{thvJA} — 145 — T _{vJsd} 150 — 195 T _{vJsd} 170 — 195 T _{vJsd} — 15 — R _{thvJC} — 10 — T _{vJsd} 150 — 10 T _{vJsd} 150 — 195 T _{vJsd} 170 — 195 |

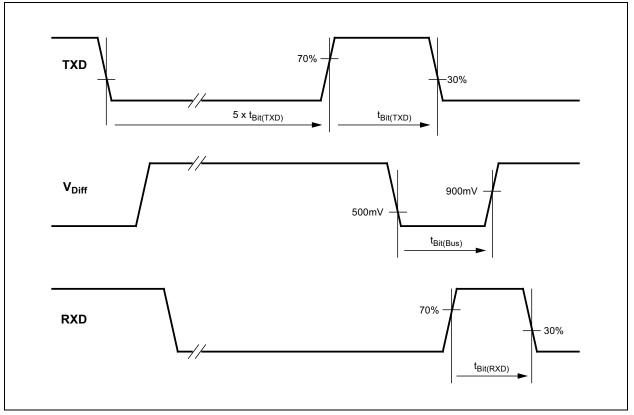






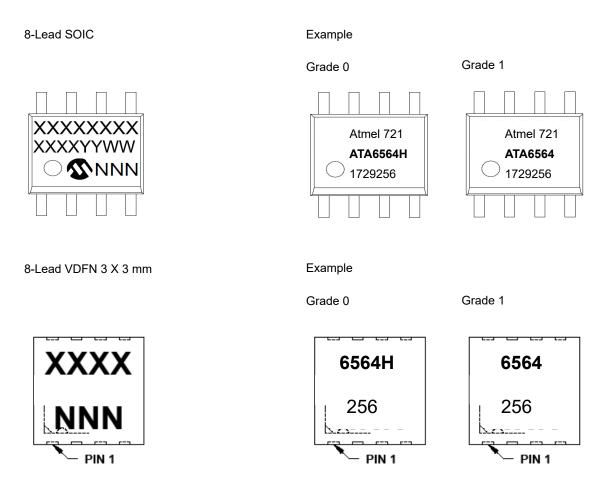






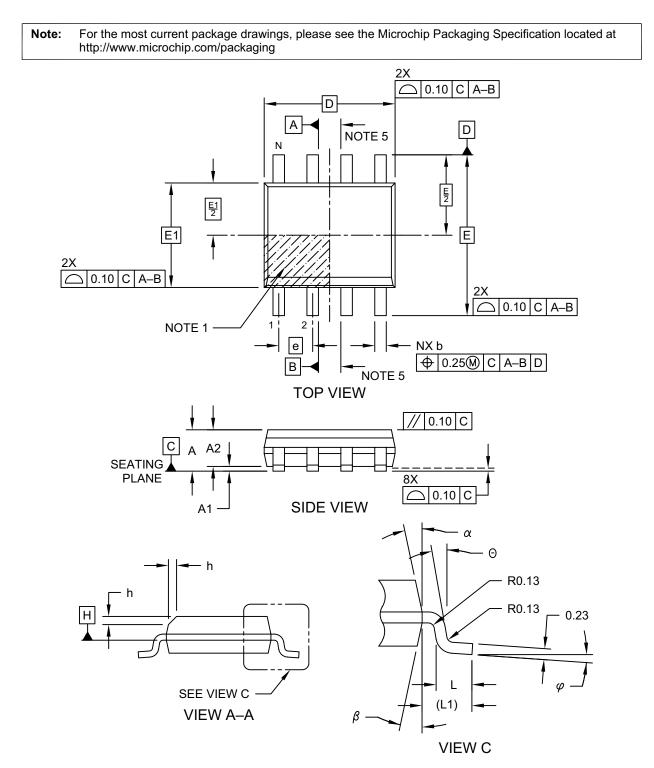
3.0 PACKAGING INFORMATION

3.1 Package Marking Information



| Legend | I: XXX Y YY WW NNN @3 * | Customer-specific information Year code (last digit of calendar year) Year code (last 2 digits of calendar year) Week code (week of January 1 is week '01') Alphanumeric traceability code Pb-free JEDEC designator for Matte Tin (Sn) This package is Pb-free. The Pb-free JEDEC designator (e3) can be found on the outer packaging for this package. |
|--------|---|--|
| Note: | be carrie | nt the full Microchip part number cannot be marked on one line, it will d over to the next line, thus limiting the number of available s for customer-specific information. |

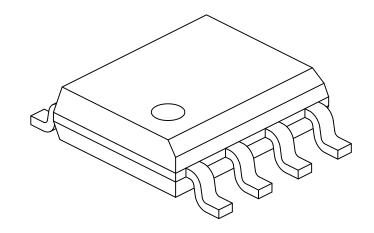
8-Lead Plastic Small Outline (OA) - Narrow, 3.90 mm (.150 In.) Body [SOIC]



Microchip Technology Drawing No. C04-057-OA Rev F Sheet 1 of 2

8-Lead Plastic Small Outline (OA) - Narrow, 3.90 mm (.150 In.) Body [SOIC]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



| | MILLIMETERS | | | | |
|--------------------------|-------------|----------|----------|------|--|
| Dimension Lin | | MIN | NOM | MAX | |
| Number of Pins | Ν | | 8 | | |
| Pitch | е | | 1.27 BSC | | |
| Overall Height | Α | - | - | 1.75 | |
| Molded Package Thickness | A2 | 1.25 | - | - | |
| Standoff § | A1 | 0.10 | - | 0.25 | |
| Overall Width | E | 6.00 BSC | | | |
| Molded Package Width | E1 | 3.90 BSC | | | |
| Overall Length | D | 4.90 BSC | | | |
| Chamfer (Optional) | h | 0.25 | - | 0.50 | |
| Foot Length | L | 0.40 | - | 1.27 | |
| Footprint | L1 | | 1.04 REF | | |
| Foot Angle | φ | 0° | - | 8° | |
| Lead Thickness | С | 0.17 | - | 0.25 | |
| Lead Width | b | 0.31 | - | 0.51 | |
| Mold Draft Angle Top | α | 5° | - | 15° | |
| Mold Draft Angle Bottom | β | 5° | - | 15° | |

Notes:

1. Pin 1 visual index feature may vary, but must be located within the hatched area.

2. § Significant Characteristic

- 3. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.15mm per side.
- 4. Dimensioning and tolerancing per ASME Y14.5M
 - BSC: Basic Dimension. Theoretically exact value shown without tolerances.

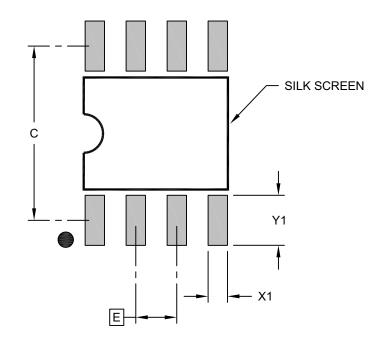
REF: Reference Dimension, usually without tolerance, for information purposes only.

5. Datums A & B to be determined at Datum H.

Microchip Technology Drawing No. C04-057-OA Rev F Sheet 2 of 2

8-Lead Plastic Small Outline (OA) - Narrow, 3.90 mm (.150 In.) Body [SOIC]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



RECOMMENDED LAND PATTERN

| | Units | | | S |
|-------------------------|----------|-----|----------|------|
| Dimensior | n Limits | MIN | NOM | MAX |
| Contact Pitch | E | | 1.27 BSC | |
| Contact Pad Spacing | С | | 5.40 | |
| Contact Pad Width (X8) | X1 | | | 0.60 |
| Contact Pad Length (X8) | Y1 | | | 1.55 |

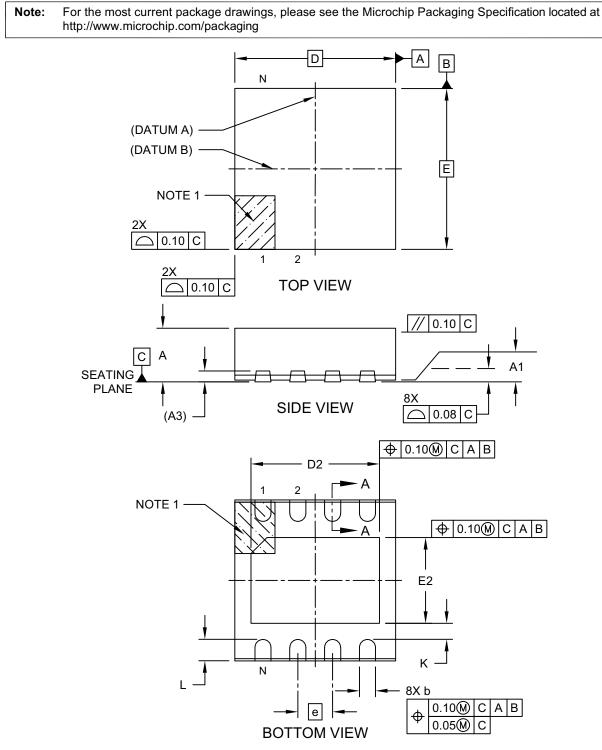
Notes:

1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing C04-2057-OA Rev F

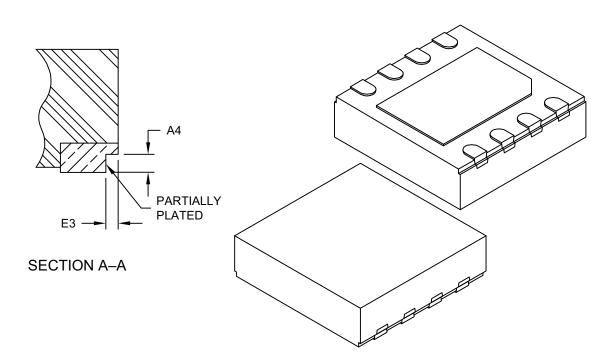
8-Lead Very Thin Plastic Dual Flat, No Lead Package (Q8B) - 3x3x1 mm Body [VDFN] With 2.40x1.60 mm Exposed Pad and Stepped Wettable Flanks; Atmel Legacy YCL



Microchip Technology Drawing C04-21358 Rev D Sheet 1 of 2

8-Lead Very Thin Plastic Dual Flat, No Lead Package (Q8B) - 3x3x1 mm Body [VDFN] With 2.40x1.60 mm Exposed Pad and Stepped Wettable Flanks; Atmel Legacy YCL

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



| | MILLIMETERS | | | | | |
|-------------------------------|-------------|--------|------------|-------|--|--|
| Dimension | Limits | MIN | NOM | MAX | | |
| Number of Terminals | N | | 8 | | | |
| Pitch | е | | 0.65 BSC | | | |
| Overall Height | Α | 0.80 | 0.90 | 1.00 | | |
| Standoff | A1 | 0.00 | 0.00 0.035 | | | |
| Terminal Thickness | A3 | | 0.203 REF | | | |
| Overall Length | D | | 3.00 BSC | | | |
| Exposed Pad Length | D2 | 2.30 | 2.40 | 2.50 | | |
| Overall Width | E | | 3.00 BSC | | | |
| Exposed Pad Width | E2 | 1.50 | 1.60 | 1.70 | | |
| Terminal Width | b | 0.25 | 0.30 | 0.35 | | |
| Terminal Length | L | 0.35 | 0.40 | 0.45 | | |
| Terminal-to-Exposed-Pad | K | 0.20 - | | - | | |
| Wettable Flank Step Cut Depth | A4 | 0.10 | - | 0.19 | | |
| Wettable Flank Step Cut Width | E3 | - | - | 0.085 | | |

Notes:

1. Pin 1 visual index feature may vary, but must be located within the hatched area.

2. Package is saw singulated

3. Dimensioning and tolerancing per ASME Y14.5M

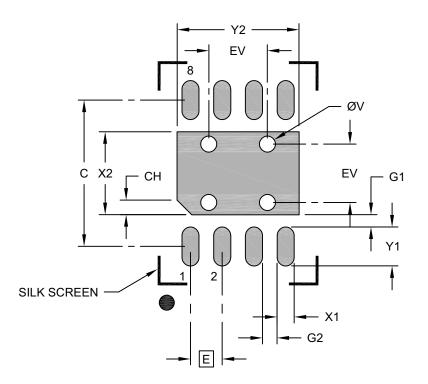
BSC: Basic Dimension. Theoretically exact value shown without tolerances.

REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing C04-21358 Rev D Sheet 2 of 2

8-Lead Very Thin Plastic Dual Flat, No Lead Package (Q8B) - 3x3x1 mm Body [VDFN] With 2.40x1.60 mm Exposed Pad and Stepped Wettable Flanks

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



RECOMMENDED LAND PATTERN

| | Units | ts MILLIMETERS | | | | |
|---------------------------------|----------|----------------|------|------|--|--|
| Dimensior | n Limits | MIN | NOM | MAX | | |
| Contact Pitch | Е | 0.65 BSC | | | | |
| Optional Center Pad Width | X2 | | | 1.70 | | |
| Optional Center Pad Length | Y2 | | | 2.50 | | |
| Contact Pad Spacing | С | | 3.00 | | | |
| Contact Pad Width (X8) | X1 | | | 0.35 | | |
| Contact Pad Length (X8) | Y1 | | | 0.80 | | |
| Contact Pad to Center Pad (X8) | G1 | 0.20 | | | | |
| Contact Pad to Contact Pad (X6) | G2 | 0.20 | | | | |
| Pin 1 Index Chamfer | СН | 0.20 | | | | |
| Thermal Via Diameter | V | | 0.33 | | | |
| Thermal Via Pitch | EV | | 1.20 | | | |

Notes:

- 1. Dimensioning and tolerancing per ASME Y14.5M
 - BSC: Basic Dimension. Theoretically exact value shown without tolerances.
- 2. For best soldering results, thermal vias, if used, should be filled or tented to avoid solder loss during reflow process

Microchip Technology Drawing C04-23358 Rev D

NOTES:

APPENDIX A: REVISION HISTORY

Revision D (December 2021)

The following is the list of modifications:

- Updated the SOIC and VDFN package drawings in Section 3.0, Packaging Information
- Updated parameter "Supply Current in Silent Mode" in "Electrical Characteristics"
- · Minor typographical edits

Revision C (August 2019)

The following is the list of modifications:

- Updated TABLE 2-1: "Temperature Specifications"
- Added test conditions at several parameters in "Electrical Characteristics"

Revision B (July 2017)

The following is the list of modifications:

- Added the new device ATA6564-GBQW0 and updated the related information across the document
- Updated ATA6564 Family Members Table.
- Corrected "Electrical Characteristics"
- Updated TABLE 2-1: Temperature Specifications
- Updated the VDFN8 package drawing and added a Grade 0 package example to Section 3.1, Package Marking Information
- Added a ATA6564-GBQW0 example to "Product Identification System" section
- Various typographical edits

Revision A (June 2017)

· Original release of this document

NOTES:

PRODUCT IDENTIFICATION SYSTEM

To order or obtain information, e.g., on pricing or delivery, contact your local Microchip representative or sales office.

| | | $\mathbf{p}_{(1)}$ | | | | Ex | amp | les: | | |
|--|-----------------|-----------------------------------|---|---------------------|--------------------------|---------|------|-------------------|--|--|
| PART NO. XX | age Tape | EXI ⁽¹⁾ and Reption | X el Package c classificat | | X Temperatur Range | a) 9 | ATA | \656 [,] | 4-GAQW0: | ATA6564, 8-Lead SOIC, Tape and Reel, package according to RoHS, Temperature Grade 0 |
| Device: Package: | ATA6564 GA = | N | ligh-speed CAN lode CAN FD F d SOIC | | ver with Silent | b) | ATA | A6564 | 4-GBQW0: | ATA6564, 8-Lead VDFN, Tape and Reel, package according to RoHS, Temperature Grade 0 |
| Tape and Reel Option: | GB = Q = | 8-Lea | d VDFN n diameter Tape | e and Reel | | c) | ATA | A6564 | 4-GAQW1: | ATA6564, 8-Lead SOIC, Tape and Reel, package according to RoHS, Temperature Grade 1 |
| Package directives classification: | W = | Packag | e according to | RoHS ⁽²⁾ | | d) | ATA | \656 [,] | 4-GBQW1: | ATA6564, 8-Lead VDFN, Tape and Reel, package according to RoHS, Temperature Grade 1 |
| Temperature Range: | 0 = 1 = | | ature Grade 0 (ature Grade 1 (| | | | Note | 1: 2: | catalog part identifier is use not printed on 1 your Microchi availability with RoHS complivalue of 0.09 and Chlorine (ppm) total Bro any homoge concentration | I identifier only appears in the number description. This ed for ordering purposes and is the device package. Check with p Sales Office for package the Tape and Reel option. ant, Maximum concentration % (900 ppm) for Bromine (Br) CI) and less than 0.15% (1500 mine (Br) and Chlorine (CI) in neous material. Maximum value of 0.09% (900 ppm) for in any homogeneous material. |

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